

20 V, dual N-channel Trench MOSFET 1 July 2015

Product data sheet

### 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance R<sub>DSon</sub> = 470 mΩ

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	ſ						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage	-		-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	600	mA
Static charac	teristics (per transistor)		÷		·	·	
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 600 mA; T <sub>j</sub> = 25 °C		-	470	620	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2	2 5	
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1	Transparent top view	S1 S2 017aaa256
7	D1	drain TR1	DFN1010B-6 (SOT1216)	
8	D2	drain TR2		

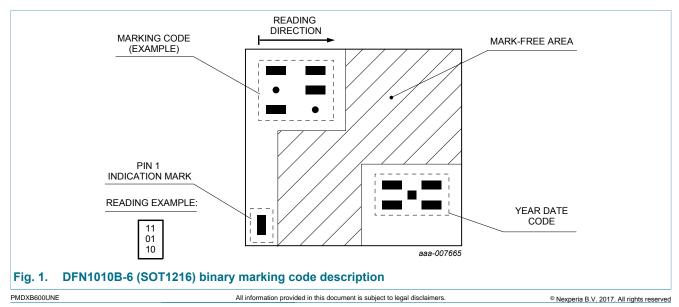
### 6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PMDXB600UNE	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216		

### 7. Marking

#### Table 4.Marking codes

Type number	Marking code
PMDXB600UNE	00 10 00



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### 8. Limiting values

#### Table 5.Limiting values

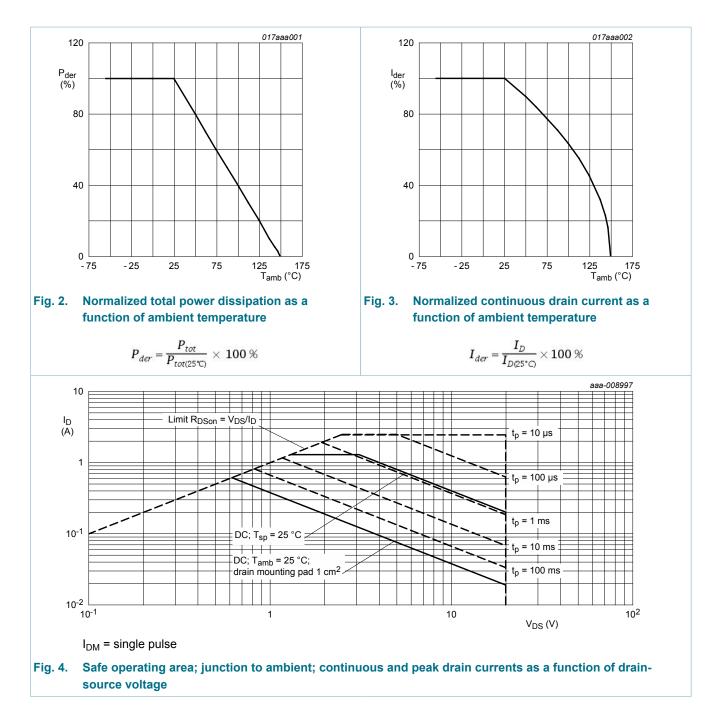
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	600	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	400	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	2.5	А
P <sub>tot</sub> total power dis	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	265	mW
			[1]	-	380	mW
		T <sub>sp</sub> = 25 °C		-	4025	mW
Source-dra	in diode		1		1	
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.4	А
Per device						
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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#### **Thermal characteristics** 9.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor						-
R <sub>th(j-a)</sub> thermal resistance	thermal resistance	in free air	[1]	-	410	475	K/W
	from junction to ambient		[2]	-	285	330	K/W

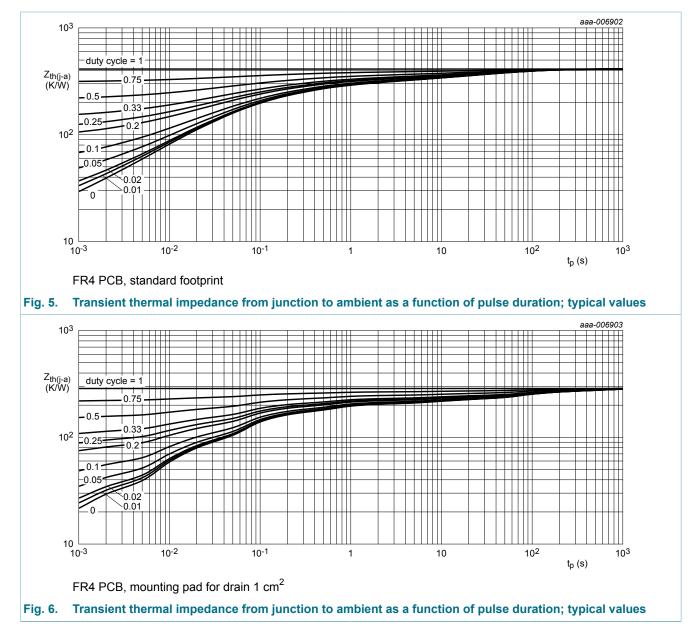
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	27	31	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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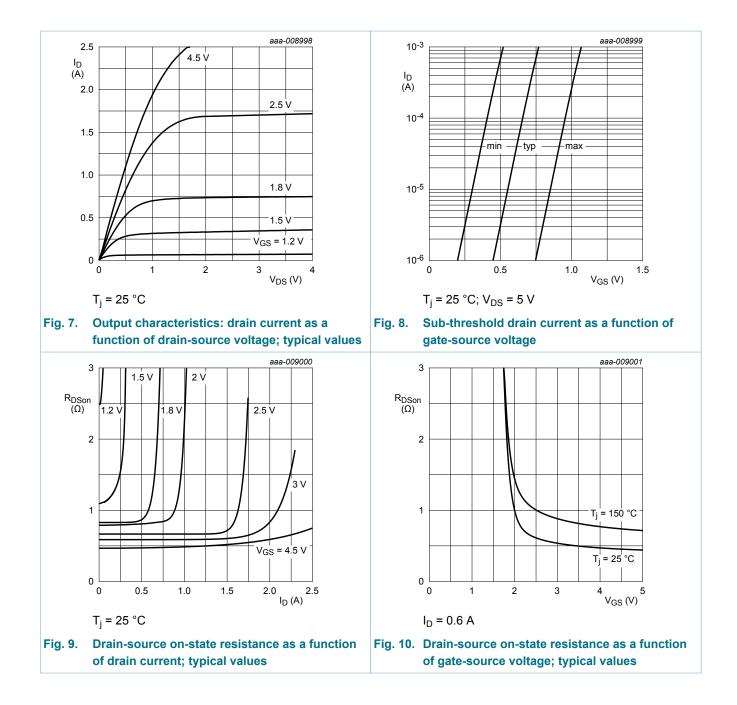
### **10. Characteristics**

Static chara V <sub>(BR)DSS</sub>	cteristics (per transistor)			Тур		
V <sub>(BR)DSS</sub>	ciensiics (per transision)					
	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = 250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	0.45	0.7	0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		$V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 600 mA; T <sub>j</sub> = 25 °C	-	470	620	mΩ
	resistance	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 600 mA; T <sub>j</sub> = 150 °C	-	760	1000	mΩ
		$V_{GS}$ = 2.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 25 °C	-	620	850	mΩ
		$V_{GS}$ = 1.8 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	845	1300	mΩ
		$V_{GS}$ = 1.5 V; I <sub>D</sub> = 10 mA; T <sub>j</sub> = 25 °C	-	1125	3000	mΩ
		V <sub>GS</sub> = 1.2 V; I <sub>D</sub> = 1 mA; T <sub>j</sub> = 25 °C	-	2210	-	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 5 V; I <sub>D</sub> = 0.6 A; T <sub>j</sub> = 25 °C	-	1	-	S
Dynamic cha	aracteristics (per transist	or)	I			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; I <sub>D</sub> = 600 mA; V <sub>GS</sub> = 4.5 V;	-	0.4	0.7	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
Q <sub>GD</sub>	gate-drain charge	_	-	0.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	21.3	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	5.4	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4.2	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; I <sub>D</sub> = 600 mA; V <sub>GS</sub> = 4.5 V;	-	5.6	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	9.2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
t <sub>f</sub>	fall time		-	51	-	ns
Source-drai	n diode (per transistor)	1		I		1
V <sub>SD</sub>	source-drain voltage	$I_{\rm S}$ = 0.36 A; $V_{\rm GS}$ = 0 V; $T_{\rm j}$ = 25 °C	-	0.8	1.2	V

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### PMDXB600UNE

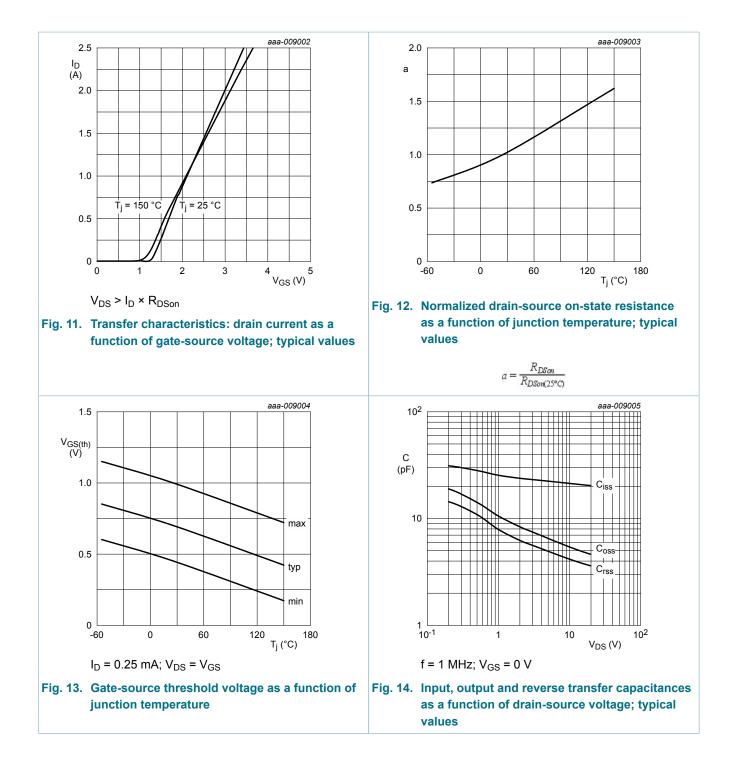
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### PMDXB600UNE

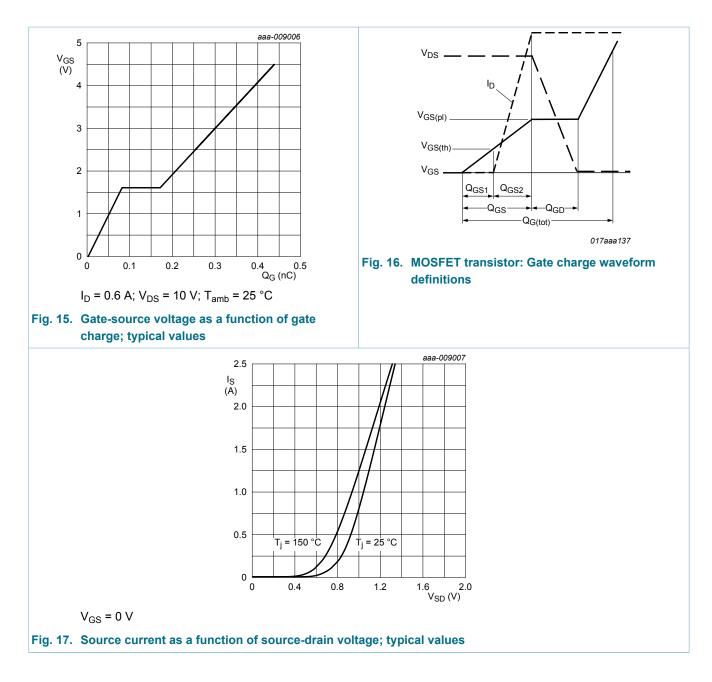
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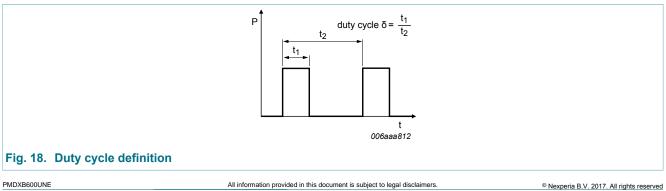
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### PMDXB600UNE

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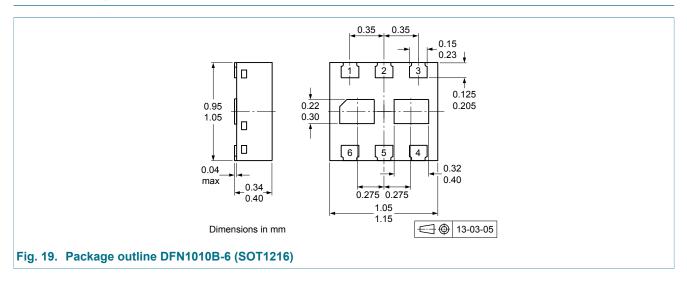


### **11. Test information**



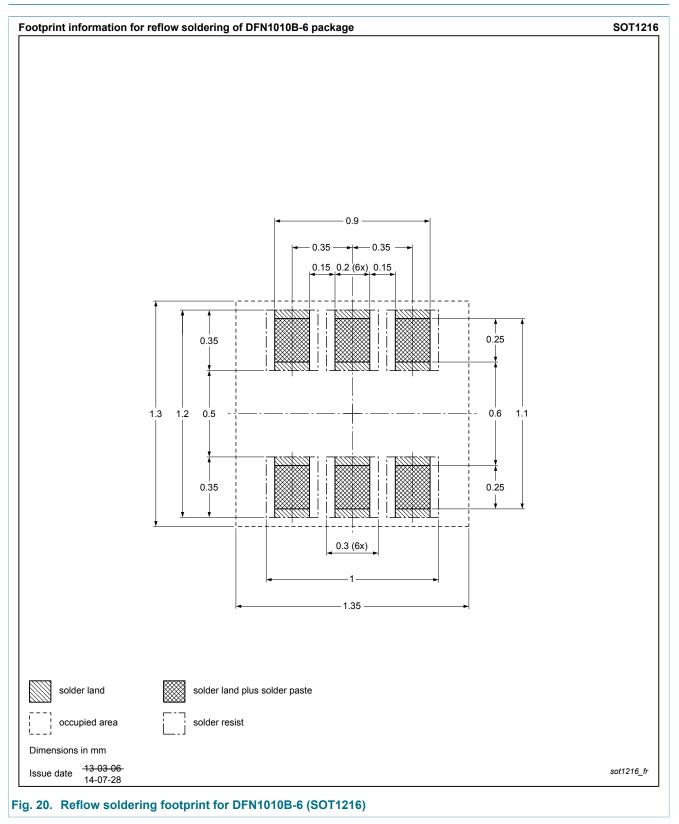
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### 12. Package outline



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### 13. Soldering



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### 14. Revision history

Table 8.Revision history				
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMDXB600UNE v.2	20150701	Product data sheet	-	PMDXB600UNE v.1
Modifications:	Change of	binary marking code posi	tion.	
PMDXB600UNE v.1	20130916	Product data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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